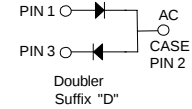
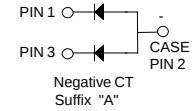
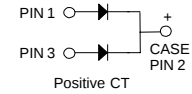
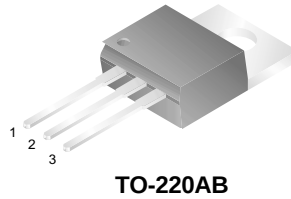




FEP16AT - FEP16JT

Features

- Low forward voltage drop.
- High surge current capacity.
- High current capability.
- High reliability.



Fast Rectifiers (Glass Passivated)

Absolute Maximum Ratings*

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value								Units
		16AT	16BT	16CT	16DT	16FT	16GT	16HT	16JT	
V_{RRM}	Maximum Repetitive Reverse Voltage	50	100	150	200	300	400	500	600	V
$I_{F(AV)}$	Average Rectified Forward Current, .375 " lead length @ $T_A = 100^\circ\text{C}$	16								A
I_{FSM}	Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-Wave	200								A
T_{stg}	Storage Temperature Range	-55 to +150								$^\circ\text{C}$
T_J	Operating Junction Temperature	-55 to +150								$^\circ\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics

Symbol	Parameter	Value	Units
P_D	Power Dissipation	8.33	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	15	$^\circ\text{C/W}$
$R_{\theta JL}$	Thermal Resistance, Junction to Lead	2.2	$^\circ\text{C/W}$

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Device								Units
		16AT	16BT	16CT	16DT	16FT	16GT	16HT	16JT	
V _F	Forward Voltage @ 8.0A	0.95				1.3		1.5		V
t _{rr}	Reverse Recovery Time I _F = 0.5 A, I _R = 1.0 A, I _{RR} = 0.25 A	35				50				ns
I _R	Reverse Current @ rated V _R T _A = 25°C T _A = 100°C	10 500								μA μA
C _T	Total Capacitance V _R = 4.0. f = 1.0 MHz	85						60		pF

Typical Characteristics

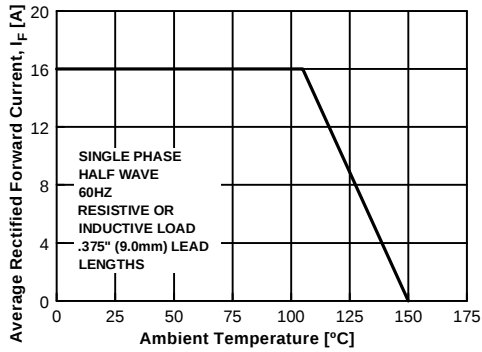


Figure 1. Forward Current Derating Curve



Figure 2. Non-Repetitive Surge Current Reverse Characteristics

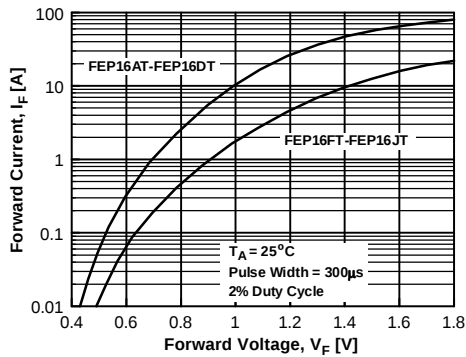


Figure 3. Forward Voltage Characteristics



Figure 4. Reverse Current vs Reverse Voltage

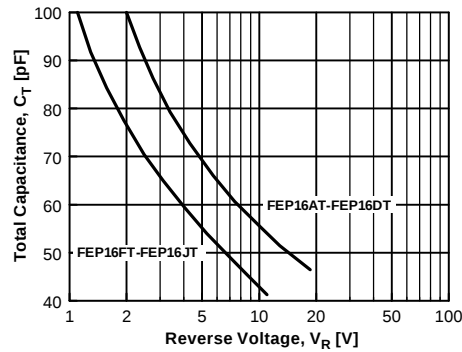
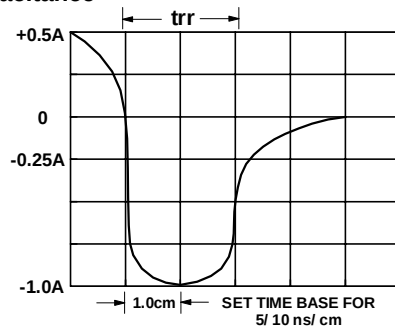
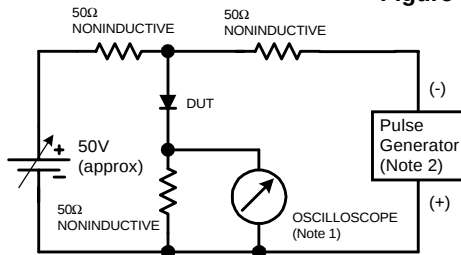


Figure 5. Total Capacitance



Reverse Recovery Time Characteristic and Test Circuit Diagram